

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI30-068	SERIAL NO. Filed herewith	<div style="writing-mode: vertical-rl; transform: rotate(180deg);">           JCS936 U.S. PTO            10/01/2005            02/05/02         </div>	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Ji Ung Lee et al.		FILING DATE Filed Herewith	
				GROUP Filed Herewith			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
✓	AA	5,482,870	Inoue			<div style="font-size: 4em; transform: rotate(45deg); opacity: 0.5;">X</div>	
↑	AB	5,372,973	Doan et al.				
	AC	5,229,331	Doan et al.				
	AD	5,210,472	Casper et al.				
	AE	4,988,638	Huang et al.				
	AF	6,057,555	Reedy et al.				
	AG	5,710,478	Kanemaru et al.				
↓	AH	6,020,683	Cathey, Jr. et al.				
✓	AI	6,249,327 B1	Murade et al.				
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
✓	AL	5-114734	Japan			X	
↑	AM	3-194937	Japan			X	
	AN	3-159250	Japan			X	
	AO	A-2-143482	Japan			X	
↓	AP	61-252687	Japan			X	
✓	AQ	A-57-85262	Japan			X	
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
✓	AR	Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuitry on Glass,					
		F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.I. Milne, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.					
✓	AS	Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Giep, Mat. Res. Soc. Symp. Proc. 148,					
		pages 283-288, 1989 Materials Research Society.					
	AT						
EXAMINER V. Y. Gusev				DATE CONSIDERED 04/26/05			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							